

## NPN-General use transistor

1W、1.5A、30V

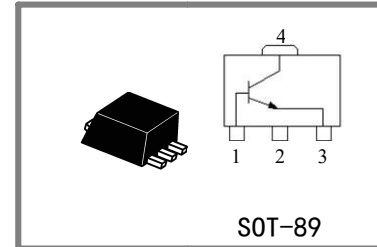
### Applications:

Can be used for switching and amplifying in various electrical and electronic equipments

### MAX RATINGS

parameters	symbol	rating	unit
collector-emitter voltage ( $I_B=0$ )	$V_{CEO}$	30	V
collector-base voltage ( $I_E=0$ )	$V_{CBO}$	40	V
emitter - base voltage ( $I_C=0$ )	$V_{EBO}$	6	V
Collector current	$I_C$	1.5	A
Total power dissipation ( $T_A=25^\circ\text{C}$ )*	$P_{tot}$	1	W
Max junction temperature	$T_{jm}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55~150	$^\circ\text{C}$

\* mounted on printed circuit board.



1: Base 2: Collector 3: Emitter

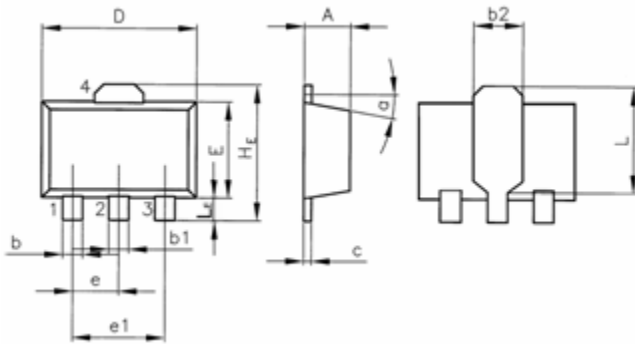
### ELECTRONIC CHARACTERISTIC (Unless otherwise specified $T_A=25^\circ\text{C}$ )

parameters		symbol	Test condition	min	typ	max	unit
collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C=2\text{mA}$ , $I_B=0$	30	—	—	V
collector- base breakdown voltage		$V_{(BR)CBO}$	$I_C=100\mu\text{A}$ , $I_E=0$	40	—	—	V
emitter - base breakdown voltage		$V_{(BR)EBO}$	$I_E=100\mu\text{A}$ , $I_C=0$	6	—	—	V
Forward current transfer ratio <sup>1)</sup>	2SC2883O	$h_{FE}$	$V_{CE}=1\text{V}$ ; $I_C=100\text{mA}$	120	—	200	—
	2SC2883Y			160	—	320	
collector-base cutoff current		$I_{CBO}$	$V_{CB}=35\text{V}$ , $I_E=0$	—	—	100	nA
emitter-base cutoff current		$I_{EBO}$	$V_{EB}=6\text{V}$ , $I_C=0$	—	—	100	nA
collector-emitter saturation voltage <sup>1)</sup>		$V_{CE(sat)}$	$I_C=800\text{mA}$ , $I_B=80\text{mA}$	—	—	0.5	V
Transition frequency		$f_T$	$I_C=50\text{mA}$ , $V_{CE}=10\text{V}$ , $f=100\text{MHz}$	—	100	—	MHz

<sup>1)</sup> pulse method:  $t_w:300\mu\text{s}$ , duty ratio  $\leq 2\%$ .

Outline dimensions (see fig.1)

unit: mm



dimensions symbols	SOT-89		
	min	typ	max
A	1.4		1.6
b	0.35		0.55
b1	0.4		0.65
b2		1.6	
c	0.35		0.45
D	4.4		4.6
E	2.35		2.55
e		1.5	
e1		3	
H <sub>E</sub>		4.15	
L		2.7	
L <sub>E</sub>		1.0	
α		5°	

Fig.1 Outline dimensions

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)